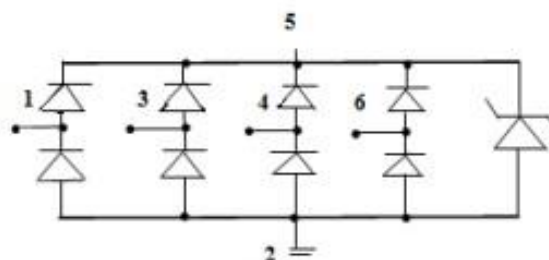
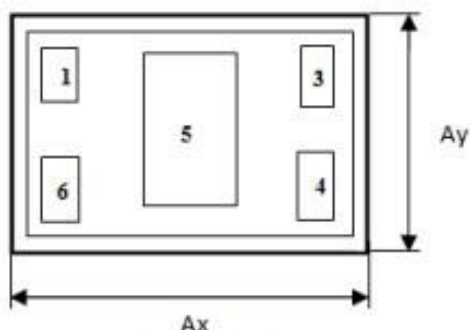



**KSR-5,0V4M5**
**KSR-5,0V4M5**

Low Capacitance TVS Diode Array.(analog SRV05-4)



**Mechanical date:**  $A_x=1000\mu\text{m}$ ;  $A_y=780\mu\text{m}$   
**Thickness** –  $138\pm 12\mu\text{m}$   
**Scribe Line width** -  $40\mu\text{m}$   
**Pin 1÷5** -Al metallization for wire bonding.  
**Pin 2** – **Back side.** Metallization Ti-Ni-Ag for soldering.

**Schematic and pinning diagram.**
**Limiting values**

Parameter	Symbol	Conditions	Value	Unit
Peak pulse power	$P_{pp}$	8/20 uS pulse per diode	350*	W
Peak pulse current	$I_{pp}$	8/20 uS pulse per diode	12*	A
Electrostatic Discharge	ESD	IEC 61000-4-2, level 4 (ESD)	>15 (air); >8 (contact)	kV
Max.junction temperature	$T_j$		150	°C

**Characteristics ( $T_j=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{RWM}$	Reverse Stand-Off Voltage. Pin 5 to 2.		-	-	5,0	V
$I_R$	Reverse leakage current. Pin 5 to 2.	$V_R=+5,0\text{ V}$	-	-	5,0	uA
$V_{BR}$	Zener diode breakdown voltage. Pin 5 to 2.	$I_Z=1\text{mA}$	5,8			V
$V_F$	Forward voltage	$I_F=15\text{mA}$	-	-	1,15	V
$V_{CL}$	Clamping Voltage Pins 1, 3, 4, 6 to 2.	$I_{pp}=1\text{A}$ , $t_{pp}=8/20\mu\text{S}$ ; $I_{pp}=5\text{A}$ , $t_{pp}=8/20\mu\text{S}$ ; $I_{pp}=12\text{A}$ , $t_{pp}=8/20\mu\text{S}$	-	-	12,0* 17,5* 30,0*	V
$C_{I/O}$	Capacitance to ground. (Pins 1, 3, 4, 6 to 2.)	$V_R=0\text{ V}$ ; $f = 1\text{ MHz}$ .	-	3,0	5,0	pF
$C_{I/O-I/O}$	Capacitance Between I/O pins.	$V_I=0\text{V}$ ; $f=1\text{MHz}$	-	1,5	-	pF

\*For Device testing